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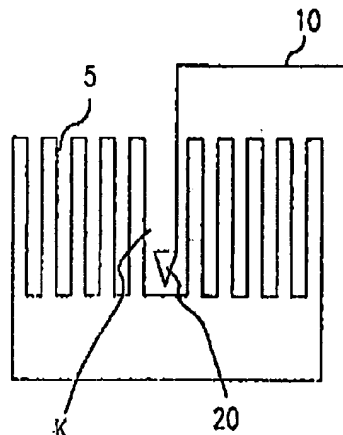
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(54) METHOD OF MEASURING A DEPTH OF A TRENCH PROFILE IN A SEMICONDUCTOR DEVICE

(57) Abstract:

PURPOSE: A method of measuring a depth of a trench profile in a semiconductor device is provided to improve productivity by forming a trench test pattern on a scribe line of the device so that an automatic force microscopy can be used.
CONSTITUTION: A method of measuring a depth of a trench profile comprises the steps of: forming a trench test pattern of which the width is wider than a trench width in a cell, on a scribe line of a semiconductor device; forming a trench mask pattern by using the trench test pattern and etching a trench on the scribe line by using the trench mask pattern; measuring a profile depth of the trench formed on the scribe line; and estimating and measuring a profile depth of the cell from the profile depth of the trench formed on the scribe line.



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